

### 140V DUAL PNP MEDIUM POWER TRANSISTOR IN SM-8

### **Description**

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

### **Features**

- BVcEo > -140V
- Ic = -0.5A High Continuous Current
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZDT795AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

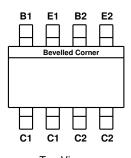
https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

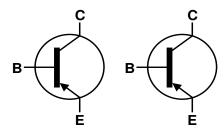
- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>®3</a>
- Weight: 0.117 grams (Approximate)







Top View Pin Out



**Equivalent Circuit** 

### **Ordering Information** (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZDT795AQTA	T795A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**

**ZETEX** ≥ T795A ≥ H H H H

SM-8

ZETEX = Product Brand Logo
T795A = Product Type Marking Code
YWW = Date Code Marking
Y = Last Digit of Year (ex: 1 = 2021)
WW = Week Code (01 to 53)



# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	VcBO	-140	V
Collector-Emitter Voltage	Vceo	-140	V
Emitter-Base Voltage	VEBO	-7	V
Continuous Collector Current	Ic	-0.5	А
Peak Pulse Current (Note 5)	I <sub>CM</sub>	-1	Α

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Power Dissipation	(Note 5)		2.25	W	
Collector Fower Dissipation	(Note 6)	PD	2.75		
Thermal Resistance, Junction to Ambient	(Note 5)	D	55.6		
Thermal nesistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	45.5	°C/W	
Thermal Resistance, Junction to Leads (Note 7)		Rejl	30.7	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

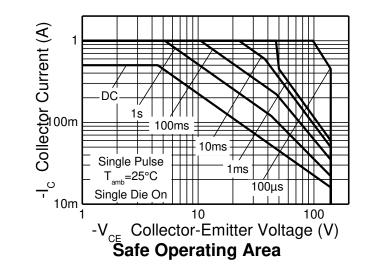
Notes:

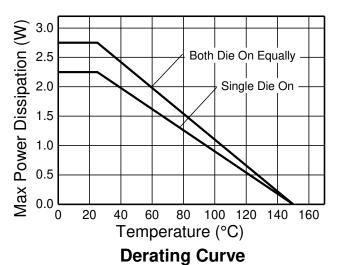
- 5. For a device with any single die active and mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as Note 5, except both die are active and equally sharing power.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

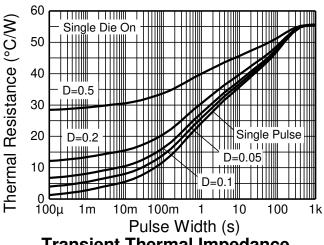
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

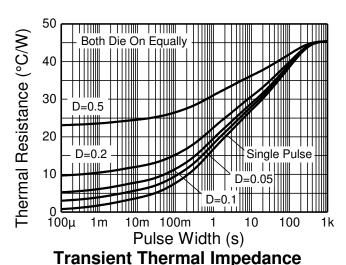


## **Thermal Characteristics and Derating Information**











W 100 Single Pulse T<sub>amb</sub>=25°C Single Pulse T<sub>amb</sub>=25°C Single Die On S

**Pulse Power Dissipation** 



# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

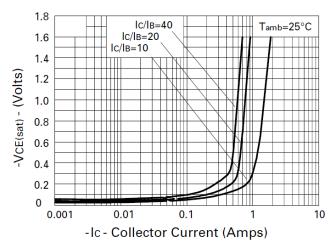
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	-140	_		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	-140	_	_	V	Ic = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	_	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	I <sub>CBO</sub>	_	_	-0.1	μΑ	V <sub>CB</sub> = -100V
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-0.1	μΑ	V <sub>EB</sub> = -5.6V
		300	_	800	] —	Ic = -10mA, VcE = -2V
DC Current Transfer Static Ratio (Note 9)	hFE	250	_			$I_C = -200 \text{mA}, V_{CE} = -2V$
		100	_	_		$I_C = -300 \text{mA}, V_{CE} = -2V$
	V <sub>CE(sat)</sub>	_	_	-0.3	V	$I_C = -100 \text{mA}, I_B = -1 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)			_	-0.3		$I_C = -200 \text{mA}, I_B = -5 \text{mA}$
		_	_	-0.25		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	_	_	-0.95	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-on Voltage (Note 9)	$V_{BE(on)}$	_	-0.75	_	V	$I_C = -500$ mA, $V_{CE} = -2$ V
Transitional Frequency	fτ	100	_	ı	MHz	$I_C = -50$ mA, $V_{CE} = -5$ V, $f = 50$ MHz
Output Capacitance	Cobo	_	15	_	pF	V <sub>EB</sub> = -10V, f = 1MHz
Switching Time	ton	ton			ns	Vcc = -50V, Ic = -100mA,
Switching Time	t <sub>off</sub>		1900	_	ns	$I_{B1} = -I_{B2} = -10 \text{mA}$

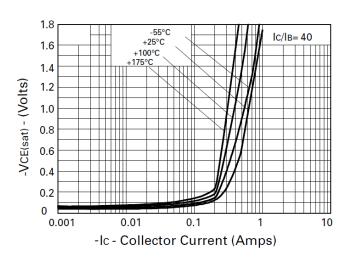
Note:

9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

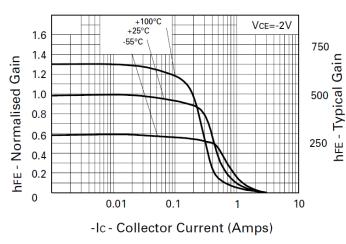


## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

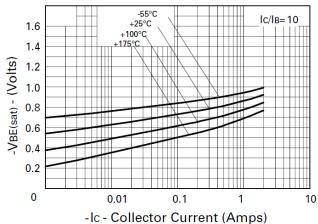




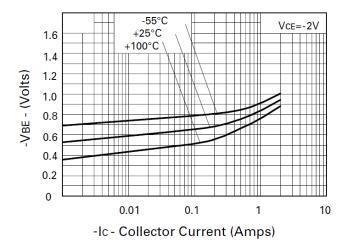
### VCE(sat) v IC







### hfe v lc



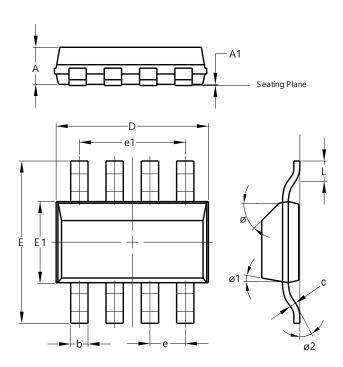
VBE(sat) v IC



# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SM-8

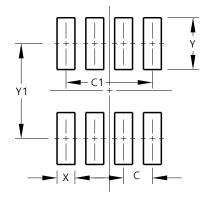


SM-8						
Dim	Min	Max	Тур			
Α		1.70	1.60			
A1	0.02	0.10	0.04			
b	0.70	0.90	0.80			
С	0.24	0.32	0.28			
D	6.30	6.70	6.60			
е	1.53 REF					
e1	4.59 REF					
Е	6.70	7.30	7.00			
E1	3.30	3.70	3.50			
L	0.75	1.00	0.90			
Ø	45°					
Ø1		15°				
Ø2			10°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SM-8



Dimensions	Value (in mm)		
С	1.52		
C1	4.6		
Х	0.95		
Υ	2.80		
Y1	6.80		



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